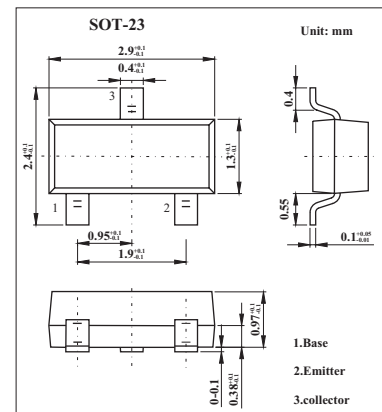


Silicon RF Switching Diode

BAT18;BAT18-04
BAT18-05;BAT18-06
■ Features

- Low-loss VHF/UHF switch above 10 MHz
- Pin diode with low forward resistance


■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Reverse Voltage	V _R	35	V
Forward Current	I _F	100	mA
Operating and storage temperature range	T _{op} , T _{stg}	-55 to +150	°C
Junction - ambient	R _{th JA}	≤450	K/W

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V _F	I _F = 100 mA		0.38	1.2	V
Reverse current	I _R	V _R = 20 V			20	nA
		V _R = 20 V, T _A = 60°C			200	
Diode capacitance	C _T	V _R = 20 V, f = 1 MHz		0.75	1	pF
Forward resistance	r _f	I _F = 5 mA, f = 100 MHz		0.4	0.7	Ω
Series inductance	L _s			2		nH

■ Marking

Type	BAT18	BAT18-04	BAT18-05	BAT18-06
Marking	A2	AU	AS	AT